# 1. General description

Double NPN switching transistor in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package.

Double PNP complement: PMBT2907AYS

### 2. Features and benefits

- Double general-purpose switching transistor
- High current (max. 600 mA)
- Voltage max. 40 V
- AEC-Q101 qualified

# 3. Applications

Switching and linear amplification

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	40	V
I <sub>C</sub>	collector current			-	-	600	mA
Per transistor							
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 150 mA; $t_{p}$ ≤ 300 $\mu$ s; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C		100	-	300	
		$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C		40	-	-	





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40 V, 600 mA, double NPN switching transistor

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter TR1	<u>654</u>	6 5 4
2	В	base TR1		P ====
3	С	collector TR2	0	TR1 TR2
4	E	emitter TR2	☐1 ☐2 ☐3	
5	В	base TR2	TSSOP6 (SOT363)	1 2 3
6	С	collector TR1		sym020

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMBT2222AYS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363		

# 7. Marking

Table 4. Marking codes

	Marking code [1]
PMBT2222AYS	BF%

[1] % = placeholder for manufacturing site code

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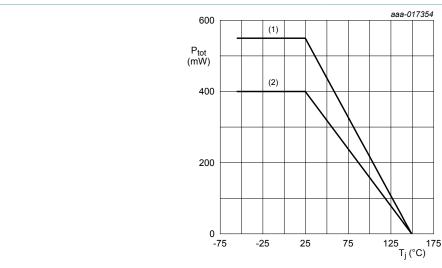
## **Limiting values**

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
$V_{CBO}$	collector-base voltage	open emitter		-	75	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	600	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	800	mA
I <sub>BM</sub>	peak base current			-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	250	mW
			[2]	-	300	mW
Per device						,
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	400	mW
			[2]	-	550	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard
- Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB; mounting pad for collector 1 cm<sup>2</sup>
- (2) FR4 PCB; standard footprint

Fig. 1. Per device: Power derating curves SOT363 (SC-88)

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### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
R <sub>th(j-a)</sub> thermal resistance in free a		in free air	[1]	-	-	500	K/W
	from junction to ambient		[2]	-	-	417	K/W
Per device	'		,			'	
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	313	K/W
from junction to ambient	from junction to ambient		[2]	-	-	227	K/W

- [1] Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

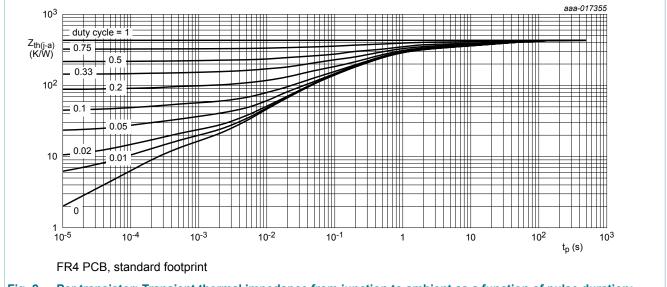


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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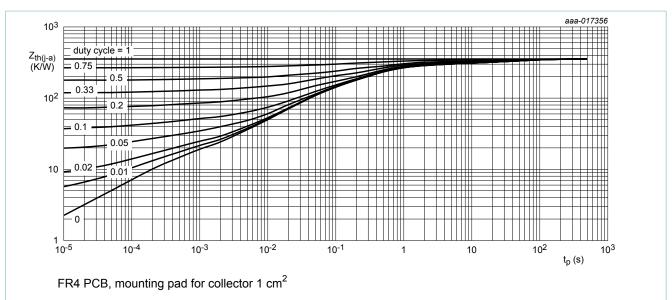


Fig. 3. Per Transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

40 V, 600 mA, double NPN switching transistor

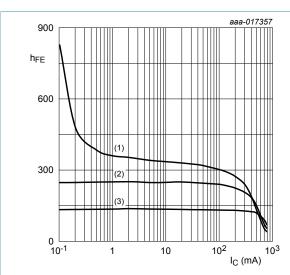
## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 60 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	10	nA
	current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}; T_j = 125 ^{\circ}\text{C}$	-	-	10	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	10	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 0.1 mA; $T_{amb}$ = 25 °C	35	-	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 1 mA; $T_{amb}$ = 25 °C	50	-	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; $T_{amb}$ = 25 °C	75	-	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 150 mA; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	100	-	300	
		$V_{CE}$ = 1 V; $I_{C}$ = 150 mA; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	50	-	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 150 mA; $I_B$ = 15 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	300	mV
		$I_{C}$ = 500 mA; $I_{B}$ = 50 mA; $t_{p}$ ≤ 300 $\mu$ s; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	1	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 150 mA; $I_B$ = 15 mA; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C	0.6	-	1.2	V
		$I_{C}$ = 500 mA; $I_{B}$ = 50 mA; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	2	V
t <sub>d</sub>	delay time	I <sub>C</sub> = 150 mA; I <sub>Bon</sub> = 15 mA;	-	-	10	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -15 mA; T <sub>amb</sub> = 25 °C	-	-	25	ns
t <sub>on</sub>	turn-on time		-	-	35	ns
t <sub>s</sub>	storage time		-	-	200	ns
t <sub>f</sub>	fall time		-	-	60	ns
t <sub>off</sub>	turn-off time		-	-	250	ns
C <sub>C</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	8	pF
C <sub>E</sub>	emitter capacitance	$V_{EB}$ = 500 mV; $I_{C}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	-	25	pF
f⊤	transition frequency	$V_{CE}$ = 20 V; $I_{C}$ = 20 mA; f = 100 MHz; $T_{amb}$ = 25 °C	300	-	-	MHz

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF	noise figure	$V_{CE}$ = 5 V; $I_{C}$ = 100 $\mu$ A; $R_{S}$ = 1 $k\Omega$ ;	-	-	4	dB
		f = 1 kHz				



 $V_{CE} = 10 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

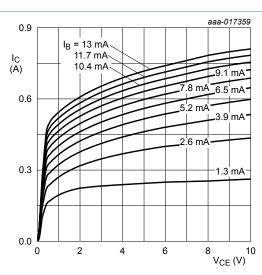
(3)  $T_{amb} = -55$  °C

(1)  $T_{amb} = -55$  °C

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb}$  = 150 °C

Fig. 4. DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values

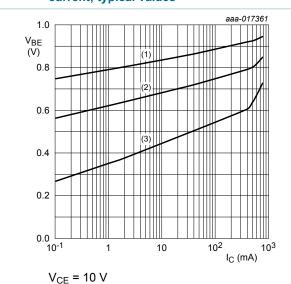
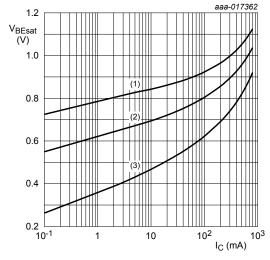


Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

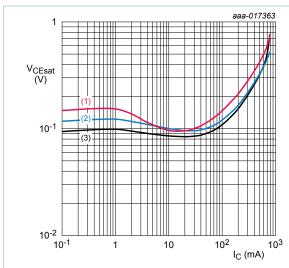
Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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#### 40 V, 600 mA, double NPN switching transistor



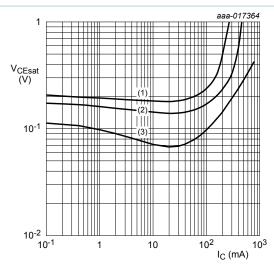
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

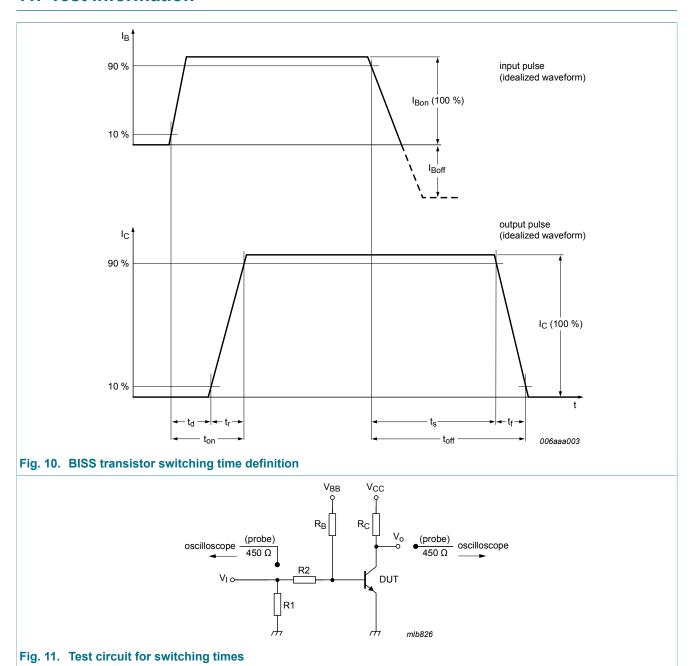
(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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### 11. Test information

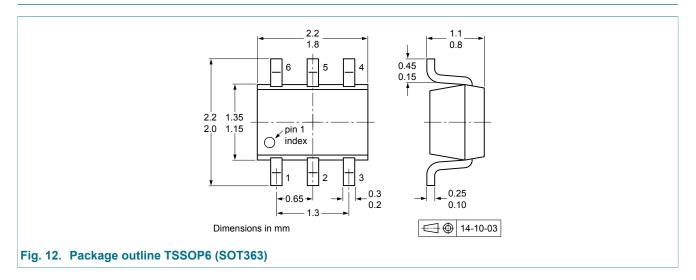


## 11.1 Quality information

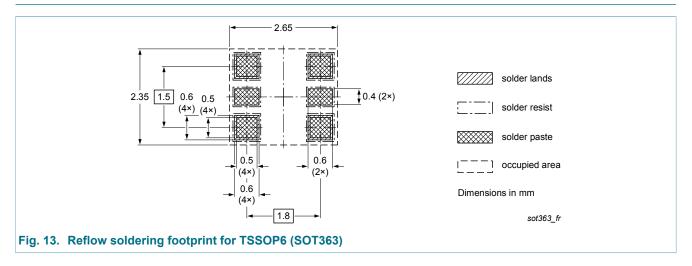
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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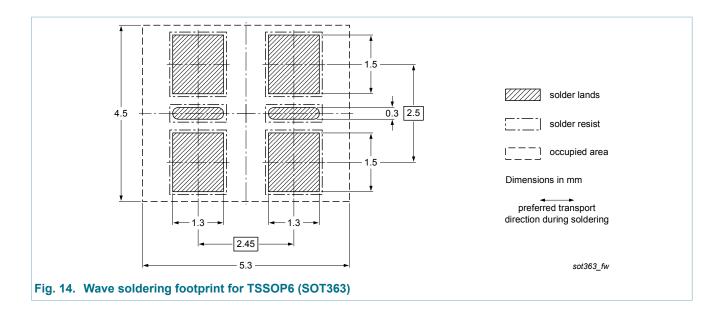
## 12. Package outline



# 13. Soldering



### 40 V, 600 mA, double NPN switching transistor



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMBT2222AYS v.1	20150624	Product data sheet	-	-

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Product [short] data sheet	Production	This document contains the product specification.

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